

**Silicon NPN transistor epitaxial type**  
**6C955**
**[ Applications ]**

General purpose amplifier

**[ Feature ]**

 Low saturation voltage  $V_{CE(sat)} = 0.5V$  (Max.) at  $I_C = 500mA$ ,  $I_B = 50mA$   
 PNP complementary pair with A5955

**[ Absolute maximum ratings (Ta=25C) ]**

Characteristic	Symbol	Maximum ratings	Unit
Collector-base voltage	VCBO	120	V
Collector-emitter voltage	VCEO	100	V
Emitter-base voltage	VEBO	6	V
Collector current	IC	1	A
Junction temperature	Tj	150	C
Storage temperature	Tstg	-55 to 150	C

**[ Electrical characteristics (Ta=25C) ]**

Characteristic	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BVCBO	120	-	-	V	$I_C = 100\mu A$
Collector-emitter breakdown voltage	BVCEO	100	-	-	V	$I_C = 10mA$
Emitter-base breakdown voltage	BVEBO	6	-	-	V	$I_E = 100\mu A$
Collector cut-off current	ICBO	-	-	500	nA	$V_{CB} = 120V$
Emitter cut-off current	IEBO	-	-	500	nA	$V_{EB} = 6V$
DC current gain 1	hFE 1	140	220	330	-	$V_{CE} = 2V$ , $I_C = 150mA$
DC current gain 2	hFE 2	40	-	-	-	$V_{CE} = 5V$ , $I_C = 1A$
Collector-emitter saturation voltage	$V_{CE(sat)}$	-	-	0.5	V	$I_C = 500mA$ , $I_B = 50mA$
Base-emitter saturation voltage	$V_{BE(sat)}$	-	-	1.1	V	$I_C = 500mA$ , $I_B = 50mA$
Transition frequency	fT	100	-	-	MHz	$V_{CE} = 5V$ , $I_E = -50mA$
Collector output capacitance	Cob	-	-	10	pF	$V_{CB} = 10V$ , $f = 1MHz$ , $I_E = 0A$

Notice 1) These are measured data of transistors assembled by PHENITEC SEMICONDUCTOR Corp. and are for reference only.

Notice 2) The contents described herein are subject to change without notice.

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